



National
Semiconductor™

Discrete POWER & Signal
Technologies

NPN Low Level Amplifiers

Device No.	Case Style	V _{CB0} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CB0} (nA) @ Max	V _{CB} (V)	I _{FE} @ Min Max	I _C & V _{CE} (mA) (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min Max	I _C (mA)	C _{ob} (pF) Max	f _T (MHz) @ Min	I _C (mA)	NF (dB) Max	Test Conditions	Process No.
MPSA18	TO-92 (92)	45	45	6.5	50	30	400 500 500 500	0.01 0.1 1 10	5 5 5 5	0.3	50	3	100	1	1.5	(Note 4)	07
2N5088	TO-92 (92)	35	30	5	50	20	300 350 300	10 1 0.1	5 5 5	0.5	10	4			3	(Note 3)	07 (5-102)
2N5089	TO-92 (92)	30	25	4.5	50	15	400 450 400	10 1 0.1	5 5 5	0.5	10	4			2	(Note 3)	07 (5-102)
2N5210	TO-92 (92)	50	50		50	35	250 250 250	10 1 0.1	5 5 5	0.7	10	4	30	0.5	3	(Note 4)	07
2N5961	TO-92 (92)	60	60	8	2	45	100 120 135	0.01 0.1 1	5 5 5	0.2	10	4	100	10	6 3 3	(Note 7) (Note 5) (Note 2)	07
2N5962	TO-92 (92)	45	45	8	2	30	450 500 550	0.01 0.1 1	5 5 5	0.2	10	4	100	10	6 4 8 3 3	(Note 6) (Note 7) (Note 8) (Note 5) (Note 2)	07
PN2484	TO-92 (92)	60	60	6	10	45	600 800 250 200 175 100 30	10 1 0.5 0.1 0.01 0.001	5 5 5 5 5 5	0.35	10	6			3	(Note 1)	07

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.

NPN Transistors

NPN Transistors

NPN Low Level Amplifiers (continued)

Device No.	Case Style	V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CB0} (nA) @ Max	V _{CB} (V)	I _{FE} @ Min Max	I _C & V _{CE} (mA) (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min Max	I _C (mA)	C _{ob} (pF) Max	f _T (MHz) Min	I _C (mA)	NF (dB) Max	Test Conditions	Process No.
PN930	TO-92 (92)	45	45	5	10	45	600 150 100	10 0.5 0.1	1	0.6 1	10	8	30	0.5	3	(Note 1)	07
2N3859A	TO-92 (94)	60	60	6	500	18	100 75	10 1				4	90	2			10
MPS6521	TO-92 (92)		25	4	50	30	300 150	2 0.1	0.5		50	3.5			3	(Note 1)	10
T1S97	TO-92 (97)		40		10	40	250 700	0.1							3	(Note 4)	10

TEST CONDITIONS

Note 1: I_C = 10 μA, V_{CE} = 5V, f = 10 Hz - 15.7 kHz.
 Note 2: I_C = 10 μA, V_{CE} = 5V, f = 10 kHz - 10 Hz, R_S = 10 kΩ.
 Note 3: I_C = 5 μA, V_{CE} = 5V, f = 1 kHz.
 Note 4: I_C = 100 μA, V_{CE} = 5V, f = 10 Hz - 15.7 kHz.
 Note 5: I_C = 10 μA, V_{CE} = 5V, f = 1 kHz, R_S = 10 kΩ.
 Note 6: I_C = 100 μA, V_{CE} = 5V, f = 1 kHz, R_S = 1 kΩ.
 Note 7: I_C = 100 μA, V_{CE} = 5V, f = 1 kHz, R_S = 10 kΩ.
 Note 8: I_C = 100 μA, V_{CE} = 5V, f = 1 kHz, R_S = 100 kΩ.